

	Type	Hits	Search Text	DBs	Time Stamp
1	BRS	1002	(substrate with "111" same epitaxial	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/03/13 12:56
2	BRS	209	((si or silicon) adj substrate with "111" same epitaxial	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/03/12 18:37
3	BRS	0	((porous) adj substrate with "111" same epitaxial	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/03/12 18:37
4	BRS	19	((substrate with "111" same epitaxial) and (solar adj cell)	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/03/12 18:38
5	BRS	5	((si or silicon) adj substrate with "111" same epitaxial) and (solar adj cell)	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/03/12 18:54
6	BRS	2	"10202887"	EPO: JPO; DERWENT	2002/03/12 19:12
7	BRS	0	(cutting adj angle) and (solar adj cell)	EPO: JPO; DERWENT	2002/03/12 19:12
8	BRS	0	(cutting adj angle) and (solar adj cell)	USPAT: US-PGPUB; EPO; JPO; DERWENT	2002/03/12 19:13
9	BRS	42	(cut with angle) and (solar adj cell)	USPAT: US-PGPUB; EPO; JPO; DERWENT	2002/03/12 19:13
10	BRS	66	(solar adj cell) and (angle with "60")	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/03/13 13:42
11	BRS	187	(process with (solar adj cell)) and (cut\$4 with cell)	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/03/13 14:03
12	BRS	2	(process with (solar adj cell)) and (cut\$4 with cell with angle)	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/03/13 13:56
13	BRS	183	(solar adj cell) and (hexagonal or triangle) and silicon	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/03/13 14:04
14	BRS	35	(solar adj cell) and (hexagonal or triangle) and ((silicon or si) adj substrate)	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/03/13 14:08
15	BRS	18	cut\$4 and ((solar adj cell) and (hexagonal or triangle) and ((silicon or si) adj substrate))	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/03/13 18:35
16	BRS	1742	"111" with ((silicon or si) adj substrate)	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/03/13 18:39
17	BRS	5135530	method or process with ("111" with ((silicon or si) adj substrate))	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/03/13 18:38
18	BRS	287	(method or process) with ("111" with ((silicon or si) adj substrate))	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/03/13 18:38
19	BRS	335	("111" with ((silicon or si) adj substrate) with p)	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/03/13 18:46
20	BRS	0	("111" near4 ((silicon or si)) with incline? with (principal adj plane))	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/03/13 18:48
21	BRS	44	("111" near4 ((silicon or si)) with incline?)	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/03/13 18:48
22	BRS	44	("111" near4 (silicon or si)) with incline?	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/03/13 19:16
23	BRS	4	("5371037" "5856229" "5869387" "61001667".PN	USPAT	2002/03/13 19:12
24	BRS	2	6180497.URPN	USPAT	2002/03/13 19:14
25	BRS	4	("111" near4 (silicon or si)) with mis?oriented	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/03/13 19:17
26	BRS	8	5302232.URPN	USPAT	2002/03/13 19:18
27	IS&R	2	("6258702".PN	USPAT: US-PGPUB; EPO; JPO; DERWENT: IBM, TDB	2002/03/18 09:38

5/6/02